



Title of Change:	Change of Au Alloy to AlTiNiAg as a new Back Metal scheme for Small Signal Transistor devices in TSOP6 package.										
Proposed first ship date:	10 November 2017 or earlier after customer approval										
Contact information:	Contact your local ON Semiconductor Sales Office or <farrah.omar@onsemi.com>										
Samples:	Contact your local ON Semiconductor Sales Office										
Additional Reliability Data:	Contact your local ON Semiconductor Sales Office or <MohdAzizi.Azman@onsemi.com>.										
Type of notification:	This is a Final Product/Process Change Notification (FPCN) sent to customers. FPCNs are issued 90 days prior to implementation of the change. ON Semiconductor will consider this change accepted, unless an inquiry is made in writing within 30 days of delivery of this notice. To do so, contact <PCN.Support@onsemi.com>.										
Change Part Identification:	After the expiration of this FPCN, devices will be produced with AlTiNiAg back metal scheme. New products will have a Date Code of WW41, 2017 or greater.										
Change category:	<input checked="" type="checkbox"/> Wafer Fab Change <input type="checkbox"/> Assembly Change <input type="checkbox"/> Test Change <input type="checkbox"/> Other _____										
Change Sub-Category(s):	<input type="checkbox"/> Manufacturing Site Change/Addition <input checked="" type="checkbox"/> Manufacturing Process Change <input checked="" type="checkbox"/> Material Change <input type="checkbox"/> Product specific change <input type="checkbox"/> Datasheet/Product Doc change <input type="checkbox"/> Shipping/Packaging/Marking <input type="checkbox"/> Other: _____										
Sites Affected:	<input type="checkbox"/> All site(s) <input type="checkbox"/> not applicable <input checked="" type="checkbox"/> ON Semiconductor site(s) : ON ISMF, Malaysia <input type="checkbox"/> External Foundry/Subcon site(s)										
Description and Purpose:	<p>ON Semiconductor is notifying customers of ISMF Fabrication facility (Seremban, Malaysia) to perform back metal scheme change (from Au Alloy to AlTiNiAg) in order to continue meeting or exceeding ON Semiconductor standards.</p> <p>The ISMF Fab facility is an ON Semiconductor owned wafer fab that has been producing products for ON Semiconductor that is TS16949, ISO-9001 and ISO-14000 certified.</p> <p>Reliability Qualification has been performed. Datasheet specifications and product electrical performance remain unchanged.</p>										
	<table border="1"> <thead> <tr> <th rowspan="2">Material to be changed</th> <th>Before Change</th> <th>After Change</th> </tr> <tr> <th>Description</th> <th>Description</th> </tr> </thead> <tbody> <tr> <td>Back Metal type</td> <td>Au Alloy</td> <td>AlTiNiAg</td> </tr> </tbody> </table>			Material to be changed	Before Change	After Change	Description	Description	Back Metal type	Au Alloy	AlTiNiAg
Material to be changed	Before Change	After Change									
	Description	Description									
Back Metal type	Au Alloy	AlTiNiAg									



Reliability Data Summary:

DEVICE NAME: SMBT35200MT1G

RMS: S30328

PACKAGE: TSOP6

Test	Specification	Condition	Interval	Results
HTRB	JESD22-A108	Ta=150°C, 100% max rated V	1008 hrs	0/231
IOL	MIL-STD-750 (M1037) AEC-Q101	Ta=+25°C, delta Tj=100°C On/off = 2 min	15000 cyc	0/231
TC	JESD22-A104	Ta= -65°C to +150°C	1000 cyc	0/231
H3TRB	JESD22-A110	85°C, 85% RH, 18.8psig, bias	1008 hrs	0/231
uHAST	JESD22-A118	130°C, 85% RH, 18.8psig, unbiased	96 hrs	0/231
PC	J-STD-020 JESD-A113	MSL 1 @ 260 °C		0/924
RSH	JESD22- B106	Ta = 265C, 10 sec		0/90
SD	JSTD002	Ta = 245C, 10 sec		0/45

Electrical Characteristic Summary:

Electrical characteristics are not impacted.

List of affected Standard Parts:

Part Number	Qualification Vehicle
MBT35200MT1G	SMBT35200MT1G
MBT35200MT2G	
NSS20201MR6T1G	
NSS20300MR6T1G	
NSS30201MR6T1G	
NSS35200MR6T1G	
NST489AMT1G	